



GP
ELECTRONICS

GPM300N06LSR
60V N-Channel MOSFET

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
60V	30mΩ@10V	6A
	36mΩ@4.5V	

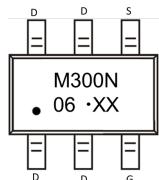
Feature

- Trench Technology Power MOSFET
- Low $R_{DS(ON)}$
- Low Gate Charge

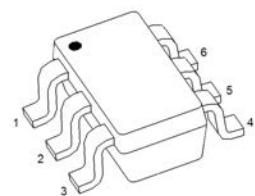
Application

- Load Switch
- DC/DC Converter

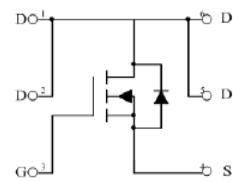
MARKING:



SOT-23-6L



Schematic diagram



ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

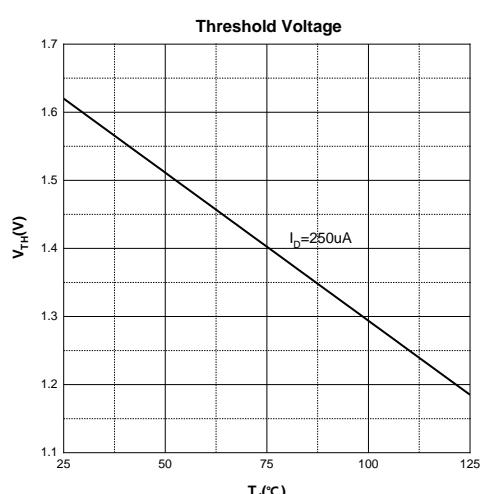
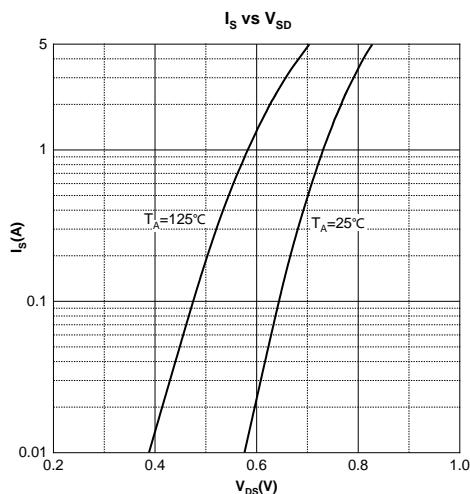
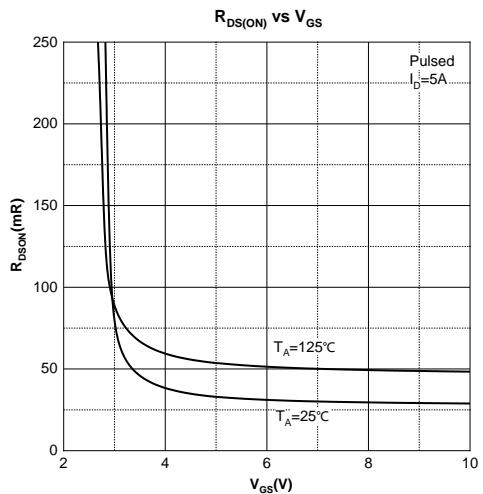
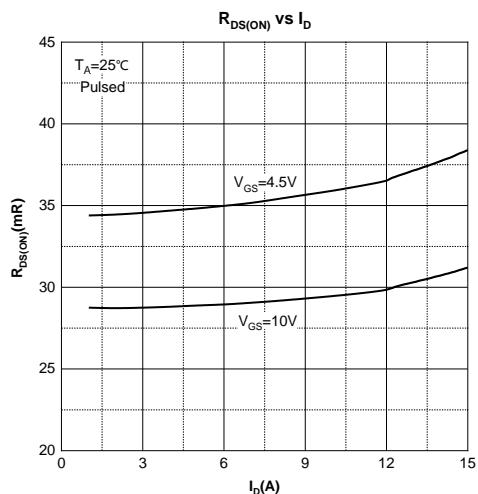
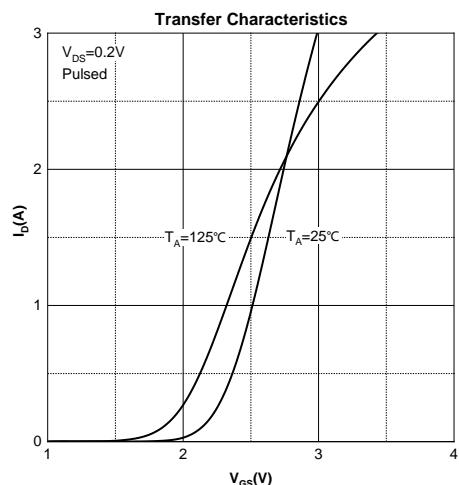
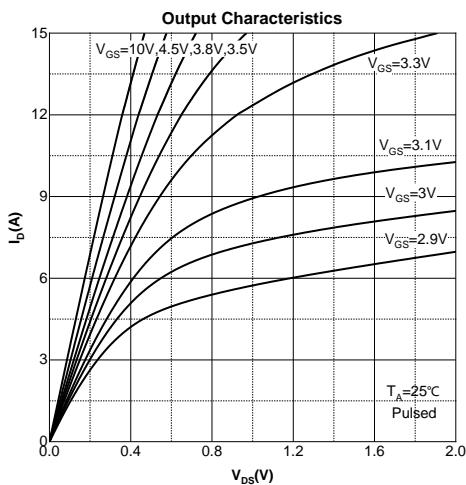
Parameter	Symbol	Value	Unit
Drain - Source Voltage	V_{DS}	60	V
Gate - Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ^{1,5}	I_D	6	A
Pulsed Drain Current ²	I_{DM}	24	A
Power Dissipation ^{4,5}	P_D	2	W
Thermal Resistance from Junction to Ambient ⁵	$R_{\theta JA}$	63	°C/W
Junction Temperature	T_J	150	°C
Storage Temperature	T_{STG}	-55~+150	°C

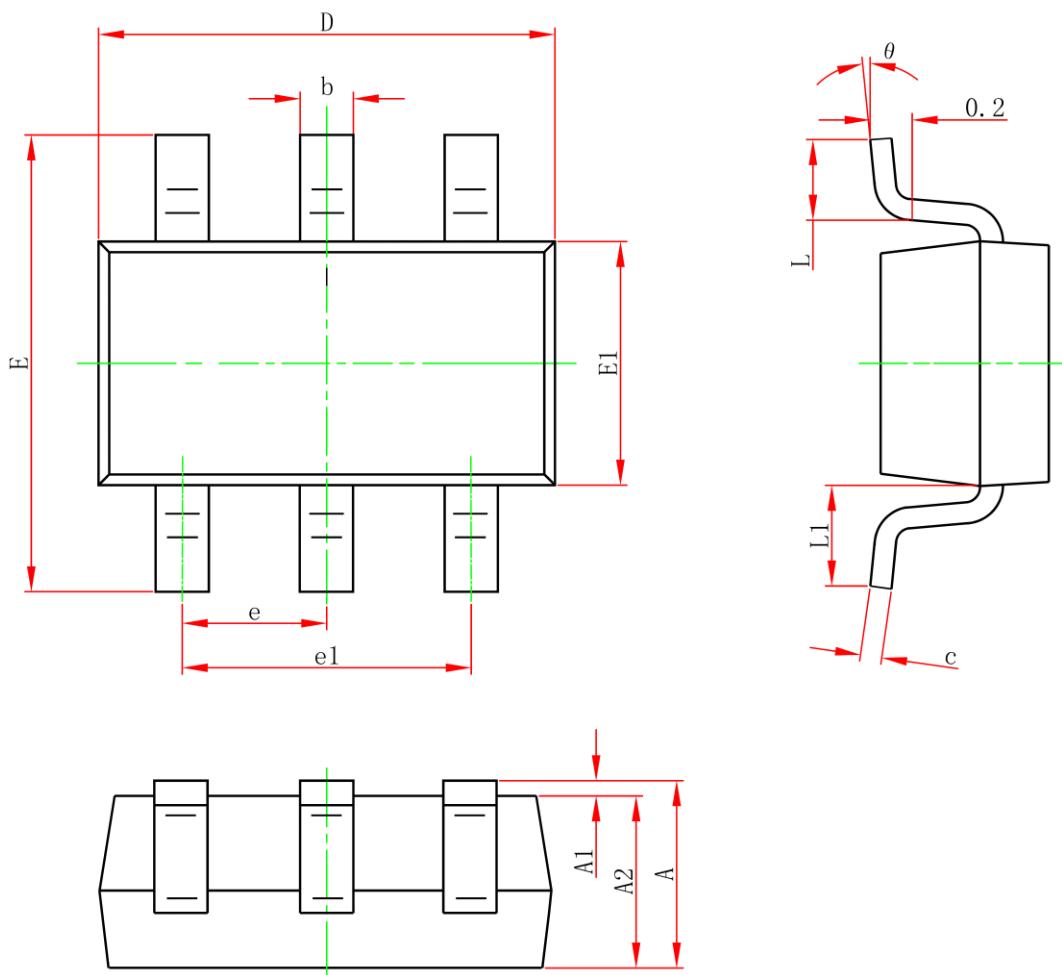
MOSFET ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Off Characteristics						
Drain - Source Breakdown Voltage	$V_{(\text{BR})\text{DSS}}$	$V_{\text{GS}} = 0\text{V}, I_D = 250\mu\text{A}$	60			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{\text{DS}} = 48\text{V}, V_{\text{GS}} = 0\text{V}$			1	μA
Gate - Body Leakage Current	I_{GSS}	$V_{\text{GS}} = \pm 20\text{V}, V_{\text{DS}} = 0\text{V}$			± 100	μA
On Characteristics³						
Gate Threshold Voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{DS}} = V_{\text{GS}}, I_D = 250\mu\text{A}$	1.0	1.6	3.0	V
Drain-source On-resistance	$R_{\text{DS}(\text{on})}$	$V_{\text{GS}} = 10\text{V}, I_D = 5.0\text{A}$		30	40	$\text{m}\Omega$
		$V_{\text{GS}} = 4.5\text{V}, I_D = 3.0\text{A}$		36	54	
Dynamic Characteristics						
Input Capacitance	C_{iss}	$V_{\text{DS}} = 30\text{V}, V_{\text{GS}} = 0\text{V}, f = 1\text{MHz}$		865		pF
Output Capacitance	C_{oss}			59		
Reverse Transfer Capacitance	C_{rss}			54		
Gate Resistance	R_g	$V_{\text{DS}} = 0\text{V}, V_{\text{GS}} = 0\text{V}, f = 1\text{MHz}$		2.2		Ω
Switching Characteristics						
Total Gate Charge	Q_g	$V_{\text{DS}} = 30\text{V}, V_{\text{GS}} = 10\text{V}, I_D = 5.0\text{A}$		20.8		nC
Gate-source Charge	Q_{gs}			2.6		
Gate-drain Charge	Q_{gd}			4.9		
Turn-on Delay Time	$t_{d(\text{on})}$	$V_{\text{DD}} = 30\text{V}, V_{\text{GS}} = 10\text{V}, R_L = 6.7\Omega, R_G = 3\Omega$		10		ns
Turn-on Rise Time	t_r			4		
Turn-off Delay Time	$t_{d(\text{off})}$			23		
Turn-off Fall Time	t_f			6		
Source - Drain Diode Characteristics						
Diode Forward Voltage ³	V_{SD}	$V_{\text{GS}} = 0\text{V}, I_s = 1.7\text{A}$			1.2	V

Notes :

- 1.The maximum current rating is limited by package.
- 2.Pulse Test : Pulse Width $\leq 10\mu\text{s}$, duty cycle $\leq 1\%$.
- 3.Pulse Test : Pulse Width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$.
- 4.The power dissipation P_D is limited by $T_{J(\text{MAX})} = 150^\circ\text{C}$.
- 5.Device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with $T_A = 25^\circ\text{C}$.

Typical Characteristics


SOT-23-6L Package Information


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.050	1.250	0.041	0.049
A1	0	0.150	0.000	0.006
A2	1.050	1.250	0.041	0.049
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E	2.650	2.950	0.104	0.116
E1	1.500	1.700	0.059	0.067
e	0.950TYP		0.037TYP	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
L1	0.600REF		0.024REF	
theta	0°	8°	0°	8°